

First passage times of charge transport and entropy change

V. V. Ryazanov

Institute for Nuclear Research, Kiev, Ukraine, e-mail: vryazan19@gmail.com

Highlights

- All real physical processes, including of the first-passage time, occur with changes in entropy.
- Changes in entropy should be taken into account when properly studying first-passage times.
- Any other changes in entropy for other possible processes can be taken into account.
- The procedure for recording the average first-passage time does not reflect the actual situation.
- The influence of entropy changes on the average *FPT* are shown.

All real physical processes, including of the first-passage time, occur with a change in entropy. This circumstance is not taken into account when studying the first-passage time, but is illustrated in this article using the example of electron transfer through a metallic double dot. The statistics of the first-passage time of a random process $N(t)$ for electrons transferred through a metallic double dot is considered. The expressions for the average first-passage time are compared with and without taking into account the change in entropy during this time. External influences on the average value of the first-passage time are considered for the case of *DC* bias voltage.

Keywords: first passage time, changes of entropy.

1. Introduction

All real physical processes that are modeled by random processes occur with a change in entropy. This also applies to first passage time (*FPT*) processes. This circumstance is not taken into account in *FPT* studies.

FPT s are widely used in various fields [1, 2]. The first-pass problem occupies a prominent place in natural science, since the *FPT* is a key characteristic of the kinetics of any process. *FPT* plays an important role in many areas of physics and applied mathematics, chemistry, protein folding, and even credit risk modeling. During *FPT*, entropy changes occur in the system. They affect *FPT*. In general, the connection between *FPT* and entropy change is considered in [3]. In this work, this connection is shown using a specific example of the process of electron transfer during mesoscopic charge transfer, based on the result of the experiment. It is shown that taking this dependence into account significantly affects the average *FPT* value.

In [4, 5], studied random times until the moment when the transfer of electric charge through a conductor reaches a given value. The *FPT* distribution of the number of electrons transferred between an aluminum conductor and a superconductor is considered. In papers [4, 5] measure the distribution of the first-passage times for the net number of electrons transferred between two metallic islands in the Coulomb blockade regime. The experimental results are consistent with the numerical calculations carried out in accordance with theory describing the distribution of the first passage time of nonequilibrium stationary Markov processes. The results of papers [4, 5] are used in this article. This article shows that the usual procedure for recording the average *FPT* does not reflect the real situation of the presence of an entropy change behind the *FPT*. An analogy can be drawn with ideal and real gases.

The core theoretical basis and approach has been explained in the author's recent paper [3]. In [3], a statistical distribution containing independent thermodynamic variables of energy and *FPT* was introduced. The factor containing the energy corresponds to the equilibrium Gibbs distribution. The nonequilibrium part of the distribution is described by a multiplier with *FPT*. Assuming that the *FPT* distribution parameters depend on the average energy values and do not depend on the random energy variable, the partition function is factorized. The factor describing the nonequilibrium part of the partition function coincides with the Laplace transform *FPT*. The Laplace transform parameter coincides with the thermodynamic parameter conjugate to *FPT* in the statistical distribution containing independent thermodynamic variables of energy and *FPT*.

The usual procedure for determining the average value of *FPT* is to differentiate the Laplace transform of *FPT* with respect to the transform parameter, after which this parameter is set equal to zero. In the approach proposed in [3], the Laplace transform parameter is equal to the thermodynamic parameter γ , which in a nonequilibrium distribution is associated with the random thermodynamic parameter *FPT*, just as the inverse temperature is associated with the random thermodynamic parameter energy. It is assumed that this is a physical quantity proportional to entropy production and fluxes [6]. This value is associated with the change in entropy in the system over *FPT*. Therefore, the average *FPT* value is written as the result of differentiating the Laplace transform *FPT* (the nonequilibrium part of the partition function) with respect to the transformation parameter. The non-zero conjugate *FPT* thermodynamic parameter, expressed through the change in entropy per *FPT*, is substituted into the resulting expression.

This paper compares the obtained expressions for the average *FPT* with a zero value of the parameter γ , conjugate to the *FPT*, and with a non-zero value of the parameter γ , expressed in terms of the change in entropy. The expressions obtained in articles [4, 5] for the distribution $P_t(N)$ for the process to take the value N at a fixed time t and the first-passage time probability distribution $P_N(t)$ for a stochastic process to first reach a given value N at time t are used, as well as the results of the experiment. An example of a *DC* bias voltage with some experimental results of [4] is considered.

In [4], a simple analytical approximation was obtained for the *FPT* distribution. Advances in nanotechnology make it possible to carry out very precise experiments with the calculation of the transferred electrons [7, 8]. Therefore, it is possible theoretically and experimentally to study the distributions of the first-passage times and waiting times [9, 10].

The second section discusses the distributions for the process to take the value N at a fixed time t and the first-passage-time probability distribution. In the third section, the approach of works [3] is briefly described. In the fourth section, this approach is applied to distribution (1) describing the first-passage times for the number of electrons transferred between two metallic islands.

2. The distribution for the process to take the value N at a fixed time t and the first-passage-time probability distribution

The fluctuations of a stochastic process $N(t)$ are usually described in terms of the distribution $P_t(N)$ for the process to take the value N at a fixed time t . An alternative approach is to study the first-passage-time probability distribution $P_N(t)$ for a stochastic process to first reach a given value N at time t . In the case of $P_t(N)$ the random variable is N at a fixed time t , and in the case of $P_N(t)$ the random variable is t at a fixed time N .

In [4, 5], the probability distribution $P_N(t)$ of the first passage is studied for the process of achieving a given value of the number of electrons N that have tunneling between two metal islands at time t . For this, the complete chronology of the events of electron transfer between two metal islands was obtained in [4, 5] (see details in [4, 5]).

The distribution of *FPT* was obtained in [4, 5] widely used in various tasks (e. g. in queue theory [11], where such distributions describe the busy interval in queuing systems). In [4] it is noted that this is a simple analytical approximation having the same structure as the random walk

result [12]. This a simple analytical expression for the distribution of the first passage time takes into account the non-Gaussian statistics of electron transport through the third cumulant of the distribution $P_t(N)$. The cumulants $P_t(N)$ are defined as $C_n = (-i)^n \partial^n \mathbb{F}(\chi) / \partial \chi^n|_{\chi=0}$, where $\mathbb{F}(\chi) = \lim_{t \rightarrow \infty} t^{-1} \ln[\sum_N e^{iN\chi} P_t(N)]$ is the cumulant generating function (CGF). If the observation time t exceeds the time τ_r required for the system to relax to a steady state after a disturbance, the CGF becomes independent of time t . The exact solution was obtained in [13].

The density of a simple analytical expression for the distribution of the first passage time is written in [4] as

$$P_N(t) = \frac{1}{t} \left| N^* \right| e^{-\frac{C_1 C_2 t}{C_3}} \left(\frac{C_2 + \sqrt{C_1 C_3}}{C_2 - \sqrt{C_1 C_3}} \right)^{N^*/2} I_{|N^*|} \left(\frac{C_1 \sqrt{C_2^2 - C_1 C_3}}{C_3} t \right), \quad (1)$$

where $N^* = [N \sqrt{C_1 / C_3}]$, C_i , $i=1,2,3$ are the cumulants of the distribution $P_t(N)$ of the process for the number N of transferred electrons at a fixed time instant t , $I_n(x)$ is the modified Bessel function of the first kind, and N is the threshold value for the number of transferred particles. The charge transferred by them, $e^* N^*$, $e^* = e \sqrt{C_3 / C_1}$ gets as close as possible to the net charge of real electrons eN , e is the electron charge. Here, the square brackets [...] indicate the rounding function.

The average electric current $\langle I \rangle$ and current noise are expressed in terms of the cumulants C_1 and C_2 , $\langle I \rangle = e C_1$, $S_I = 2 \int dt \langle I(t) I(0) - \langle I \rangle^2 \rangle = 2e^2 C_2$. The C_3 and C_4 values represent the third and fourth cumulants of the distribution $P_t(N)$. In [4], it was also assumed that $C_1, C_3 > 0$, and $C_2^2 > C_1 C_3$. Distribution (1) was obtained in [4] from a general approach with some approximations (for sufficiently large times, an approximate form of the cumulant generating function). In [4], was noted that expression (1) is fulfilled under the conditions

$$\frac{C_1 |C_1 C_4 - C_2 C_3|}{12 C_2^3} \left(\frac{N}{C_1 t} - 1 \right)^2 \leq 1, \quad t \gg \tau_r, \quad |N| \gg 1. \quad (2)$$

In accordance with the first condition (2), relation (1) is fulfilled better near the maximum of the distribution $P_N(t)$, at $t = N/C_1$, than in the tails of the distribution. The time required for the system to return to a stationary state after an external disturbance is defined as the relaxation time τ_r .

At short times expression (1) behaves like $t^{|N^*|-1}$. When the inequality holds $|C_3 - C_1| \leq C_1$, it reproduces the scaling of the exact distribution $P_N(t) \sim t^{|N|-1}$ for small values of N . In this case, the last of conditions (2) can be weakened. At long times Eq. (1) correctly reproduces the exponential decay $P_N(t)$ predicted by the exact theory [13], but may give an inaccurate decay rate if the first of conditions (2) are violated. Further, in the Gaussian limit $C_3 \rightarrow 0$ distribution (1) reduces to the form known from the theory of Brownian motion.

The approximate distribution (1) satisfies the fluctuation relation $\frac{P_N(t)}{P_{-N}(t)} = \left(\frac{C_2 + \sqrt{C_1 C_3}}{C_2 - \sqrt{C_1 C_3}} \right)^{[N \sqrt{C_1 / C_3}]}$ which does not require the system to be in equilibrium or to exhibit detailed balance, and relies only on the conditions (2). In the limit $t \gg \tau_r$, and provided the system has a well-defined temperature T , one can also prove an exact fluctuation relation, $P_N(t) / P_{-N}(t) = \exp[NeV_b / k_B T]$ which is a consequence of the fluctuation theorem for the electron transport and remains valid for quantum conductors described by the Schrödinger equation.

3. Relationship between FPT and entropy change.

In [5] experimentally studied fluctuations of stochastic entropy production of the electric current in non-equilibrium steady-state conditions in an electronic double dot. In this paper, we

consider the thermodynamic aspects of *FPT* moments, in particular, the relationship between the first moment and the entropy change accompanying the first achievement process.

The *FPT* moments classified in the theory of stochastic processes as stopping times and Markov moments [14, 15]. The set of events observed during the random time *FPT* $T_{\gamma x}$ (3) [15] corresponds to a set describing Markov moments. This takes into account the dependence on the history of the system. The change in the entropy of the system depends on the events occurring at this time. *FPT* (3) is a multiplicative functional of a random process $X(t)$ [14]. Dependence on the system's past is important in distribution (4), (5).

In this work, arbitrary changes in entropy taken into account, which affect the moments of the process of *FPT*. Using distribution (1) makes it possible to accurately calculate the impact on the system. Changes in entropy are expressed through entropy flows into the system from the outside and entropy production in the system. The production of entropy is equal to the product of thermodynamic forces and the thermodynamic flows created by these forces. The actions on the system are also described by thermodynamic forces and entropy changes.

The distribution of the first-passage time for the number of electrons reaching a certain threshold was obtained in [4]. In [3], the argument of the Laplace transform of the *FPT* distribution is related to the change in the entropy of the system using thermodynamic relations. The average *FPT* value, in which the value of the argument of the Laplace transform of the *FPT* distribution is assumed to be zero, does not correspond to real events in which the changes in entropy and the value of this argument are not equal to zero. The task is to determine the value of the argument of the Laplace transform corresponding to the change in entropy in the real *FPT* process of reaching a given level.

The change in entropy is expressed in terms of thermodynamic flows and conjugate thermodynamic forces. The inverse relationship is also true: *FPT* affected by entropy changes caused by the introduction or change of thermodynamic forces. It is possible to formulate and study the *FPT* control problem. System entropy and *FPT* change with changes in thermodynamic forces. The processes in the system slow down or speed up.

An external *DC* voltage V_b is considered as external thermodynamic forces. Non-equilibrium fluctuations of the charge-state in a hybrid double point normal metal-superconductor in the regime of strong Coulomb blockade, subject to the influence of a time-independent bias voltage, were measured in [4, 5]. An external *DC* bias voltage, V_b , which causes the system to go to a non-equilibrium steady state and controls the net current through the double-dot, is applied between the two leads.

In [3, 16-19] the *FPT* considered. *FPT* is defined as the time during which the random process $X(t)$ first reaches a certain threshold a (3). *FPT* is by definition equal to

$$T_{\gamma x} = \inf\{t : X(t) = a\}, X(0) = x > 0. \quad (3)$$

The subscript γ , emphasizing the dependence on the conjugate thermodynamic parameter, is used not to confuse the variable with the temperature T . There are other definitions of *FPT* [14, 15]. A distribution that contains *FPT* ("lifetime" in [19]) as an additional thermodynamic parameter is introduced in [3, 16-19]. The microscopic probability density in the extended phase space with cells (u, T_γ) (by extended phase space we mean the phase space, the hypersurface in the phase space containing fixed values of u and T_γ compared to the hypersurface in the phase space containing only fixed values of u , as in the equilibrium case), where u and T_γ are thermodynamic variables, has the form

$$\rho(z; u, T_\gamma) = \exp\{-\beta u - \gamma T_\gamma\} / Z(\beta, \gamma), \quad (4)$$

where $\beta = 1/T$ is the inverse temperature of the reservoir ($k_B = 1$, k_B is Boltzmann constant), ($z = q_1, \dots, q_N, p_1, \dots, p_N$) are dynamic variables, q and p are the coordinates and momenta of N particles of the system, the partition function is equal

$$Z(\beta, \gamma) = \int e^{-\beta u - \gamma T_\gamma} dz = \iint du dT_\gamma \omega(u, T_\gamma) e^{-\beta u - \gamma T_\gamma}. \quad (5)$$

The factor $\omega(u)$ in the case of a distribution for u is replaced by $\omega(u, T_\gamma)$ [3]. If $\mu(u, T_\gamma)$ is the number of states in the phase space with parameter values less than u and T_γ , then

$\omega(u, T_\gamma) = d^2 \mu(u, T_\gamma) / du dT_\gamma$. Moreover, $\int \omega(u, T_\gamma) dT_\gamma = \omega(u)$. The number of phase points with parameters in the interval between $u, u+du$; $T_\gamma, T_\gamma+dT_\gamma$, is $\omega(u, T_\gamma) du dT_\gamma$. The parameters β and γ are the Lagrange multipliers. They satisfying the following expressions for the averages:

$$\langle u \rangle = -\partial \ln Z / \partial \beta_\gamma; \quad \langle T_\gamma \rangle = -\partial \ln Z / \partial \gamma_\beta. \quad (6)$$

The values of energy u and *FPT* T_γ in expressions (4)-(6) are chosen as thermodynamic parameters. The production and flows of entropy characterize non-equilibrium processes in an open statistical system. Associated with them is the conjugate *FPT* parameter γ . The non-equilibrium distribution (4) converges to equilibrium Gibbs distribution at $\gamma=0$ and $\beta=\beta_0=T_{eq}^{-1}$, where T_{eq} is the equilibrium temperature.

The factor $\omega(u, T_\gamma)$ is the joint probability for u and T_γ , considered as the stationary probability of this process. We rewrite the value $\omega(u, T_\gamma)$ in the form

$\omega(u, T_\gamma) = \omega(u) \omega_1(u, T_\gamma) = \omega(u) \sum_{k=1}^n R_k f_{1k}(T_\gamma, u)$. It is assumed that there are n classes of states in the system; R_k is the probability that the system is in the k -th class of states, $f_{1k}(T_\gamma, u)$ is the density of the distribution of *FPT* T_γ in this class of (ergodic) states (in the general case, $f_{1k}(T_\gamma, u)$ depends on u). As a physical example of such a situation (characteristic of metals, glasses, etc.), one can mention the potential of many complex physical systems. Below we restrict ourselves to the case $n=1$.

The local specific entropy s corresponding to distribution (4) (u is the specific internal energy) is introduced by the relation [3]

$$s = -\langle \ln \rho(z; u, T_\gamma) \rangle = \beta \langle u \rangle + \gamma \langle T_\gamma \rangle + \ln Z(\beta, \gamma); \quad ds = \beta d\langle u \rangle + \gamma d\langle T_\gamma \rangle \quad (7)$$

($s \rightarrow s/k_B$, entropy is divided by k_B , Boltzmann's constant). This is the entropy produced in the system. We assume that in (5) $\omega(u, T_\gamma) = \omega(u) \omega_1(u, T_\gamma)$, $\omega_1(u, T_\gamma) \sim f(T_\gamma, u)$ [3]. Here $f(T_\gamma, u)$ is the *FPT* distribution density. Suppose that this function does not depend on the random energy u (possible dependence on the average energy value). Then the variables of integration are separated. The partition function statistical sum (5) is written as the product of equilibrium and non-equilibrium factors, $Z(\beta, \gamma) = Z_\beta Z_\gamma$. The non-equilibrium part of the partition function Z_γ is the Laplace transform of the *FPT* distribution density. For internal energy and partition function the following relations are fulfilled:

$$Z(\beta, \gamma) = Z_\beta Z_\gamma, \quad Z_\beta = \int e^{-\beta u} \omega(u) du, \quad Z_\gamma = \int_0^\infty e^{-\gamma T_\gamma} f(T_\gamma) dT_\gamma. \quad (8)$$

From expressions (7)-(8), we obtain an equation for determining the non-equilibrium parameter γ conjugated to the *FPT*:

$$s = s_\gamma + s_\beta = s_\beta - \Delta = \gamma \bar{T}_\gamma + \beta \bar{u} + \ln Z = \beta \bar{u} + \ln Z_\beta - \Delta, \quad -\Delta = s_\gamma = s - s_\beta, \quad -\Delta = s_\gamma = \beta u_\gamma + \gamma \bar{T}_\gamma + \ln Z_\gamma, \quad (9)$$

$$\bar{u} = -\frac{\partial \ln Z}{\partial \beta} = u_\beta + u_\gamma, \quad u_\beta = -\frac{\partial \ln Z_\beta}{\partial \beta} \Big|_\gamma, \quad u_\gamma = -\frac{\partial \ln Z_\gamma}{\partial \beta} \Big|_\gamma = \int_0^\infty e^{-\gamma T_\gamma} \left(-\frac{\partial f(T_\gamma)}{\partial \beta} \right) dT_\gamma \frac{1}{Z_\gamma},$$

where $s_\beta = \beta \bar{u}_\beta + \ln Z_\beta$, $s_\gamma = \beta u_\gamma + \gamma \bar{T}_\gamma + \ln Z_\gamma$, $s_\beta = s|_{\gamma=0}$, Z_β is “stationary” partition function; u_β is “stationary” energy; s_β is “stationary” entropy. Expression (7) describes the Gibbs-Shannon entropy and is related to the production of entropy in the system. Relations (6)-(9) are applied below to distribution (1).

4. Time elapsed until the electric charge transferred through a conductor reaches a given threshold value. Comparison of theory with experimental data

In [12, 20], an exact result was obtained for a one-dimensional biased random walk:

$$P_N(t) = \frac{1}{t} |N| e^{-(\Gamma_+ + \Gamma_-)t} \left(\frac{\Gamma_+}{\Gamma_-}\right)^{N/2} I_N(2\sqrt{\Gamma_+ \Gamma_-} t). \quad (10)$$

In [4] at $\Gamma_{\pm} = \frac{C_1}{2C_3} (C_2 \pm \sqrt{C_1 C_3})$, expression (1) is written. Here Γ_{\pm} are the rates of jumping forward and backward. In [21], this model describes the transport of charged particles through a voltage biased tunnel junction. In [4], from (1)-(2), approximations were obtained for short times, for small values of N , for large times, as in the exact theory [13, 22], for a weakly non-Gaussian random process, as well as for the Gaussian limit.

In [4], the predictions of the exact theory [13, 20, 22] were compared with experimental results. A perfect agreement was found at sufficiently long times determined by expression (2). In [4], a simple and universal approximation was also written for the *FPT* distribution (1) taking into account the non-Gaussian statistics of one-electron tunneling using the third cumulant C_3 of the distribution of the number of transmitted electrons.

The Laplace transform of the distribution (1) has the form

$$Z_{s(\gamma)} = \frac{(2\Gamma_+)^{N^*}}{(s + \Gamma_{\Sigma} + \sqrt{(s + \Gamma_{\Sigma})^2 - 4\Gamma_+ \Gamma_-})^{N^*}}, \quad \Gamma_{\Sigma} = \Gamma_+ + \Gamma_- = \frac{C_1 C_2}{C_3}, \quad \Gamma_+ - \Gamma_- = \frac{C_1^{3/2}}{C_3^{1/2}}, \quad (11)$$

$$\Gamma_+ \Gamma_- = \frac{C_1^2}{4C_3^2} (C_2^2 - C_1 C_3).$$

The mean value of *FPT* determined from expressions (6), (8), (11) is equal to ($s=\gamma$)

$$\bar{T}_{\gamma} = \frac{N^*}{\sqrt{(s + \Gamma_{\Sigma})^2 - 4\Gamma_+ \Gamma_-}} = \frac{T_0}{\sqrt{1 + \frac{s(s + 2\Gamma_{\Sigma})}{(\Gamma_+ - \Gamma_-)^2}}}, \quad T_0 = \bar{T}_{\gamma=0} = \frac{N^*}{\Gamma_+ - \Gamma_-} = \frac{N}{C_1}. \quad (12)$$

Using relations (12), the calculations are carried out and the expressions for \bar{T}_{γ} , the average FPT for non-zero values of $\gamma(\Delta)$, the parameter γ , which depends on the change in entropy Δ from (9), and the expression for T_0 for zero values of Δ and $\gamma(\Delta)$ are compared with each other.

By $\gamma \geq 0$, $\bar{T}_{\gamma} \leq T_0$. We seek the dependence $\gamma(\Delta)$ from equation (9). Expressions for Γ_+ and Γ_- are written in [4, 5]. So, the expression for Γ_+ has the form

$$\Gamma_+ = \Gamma_{L \rightarrow R}(\Delta E) = \frac{1}{e^2 R} \int dE n_L(E) n_R(E - \Delta E) f_L(E) (1 - f_R(E - \Delta E)), \quad (13)$$

where $\Delta E = -eV_b$. Here $R=R_{nm}$ is the resistance of the transition in which the electron jump occurs, $n_i(E)$ and $f_i(E)$ are the density of states and the distribution function in the initial electrode, $n_f(E)$ and $f_f(E)$ are the density of states and the distribution function in target electrode (is Fermi function). The density of states in superconductors has the usual form $n_s(E) = \theta(|E| - \Delta_1) |E| / \sqrt{E^2 - \Delta_1^2}$, where Δ_1 is the superconducting gap, and in normal metals it is equal to 1. The corresponding rates are obtained in [23-25].

The rates can be conveniently expressed in the form [26]:

$$\Gamma_+ = \Gamma_d e^{-\beta e V_b / 2}, \quad \Gamma_- = \Gamma_d e^{\beta e V_b / 2}. \quad (14)$$

In accordance with the general approach to diffusion in an external field [27], we write the value Γ_d in the form $\Gamma_d = \Gamma_0 e^{-\beta E_a}$, where E_a is the maximum potential energy between the "electron islands". In [5] and [28] the expression for electrostatic energy in an electronic double dot is written. In case $V_b=0$

$$E_{dot}(n) = \frac{E_{C_1}}{2} (n_L - n_{g,L})^2 + \frac{E_{C_2}}{2} (n_R - n_{g,R})^2 + E_{C,m} (n_R - n_{g,R})(n_L - n_{g,L}), \quad (15)$$

where E_{C_1}, E_{C_2} are the charging energies of the islands, $E_{C,m}$ is the electrostatic coupling energy, $n_L, n_R, n_{g,L}, n_{g,R}$ are the charge and gates charge states of the left and right dots.

For simplicity, let's take the values $V_{gL}=V_{gR}=0$, $n_{gL}=n_{gR}=0$, $n_L=n_R=1/2$. From [5] we take the values $E_{CL}=E_{C_1}=60 \mu eV$, $E_{CR}=E_{C_2}=40 \mu eV$, $E_{C_m}=10 \mu eV$. Then from (15) we obtain $E_{dot}=15 \mu eV$, $T_{eff}=1,175 K$, $\beta^{-1}=k_B T_{eff}=1,6215 \cdot 10^{-23} J$, $\beta E_a=0,148$. Value $T_{eff}=1,175 K$ taken from Table 1 [5] as an average T_{eff} for voltages $V_b=25 \mu V$ and $V_b=-25 \mu V$.

In the course of reaching the boundary N by the random process $N(t)$, the entropy of the system [5] changes by the value $\Delta=\Delta_e$. These changes must be taken into account. Therefore, one cannot assume in (12) $\gamma=0$, considering the value of T_0 as the average value of the time of the first achievement in the absence of impacts on the system. An internal change in entropy Δ_e occurs and in the absence of any external influences in the system. The value of Δ_e can be determined, for example, from the relations of extended irreversible thermodynamics [29] $\Delta_e=\tau_e i i / 2 \rho \sigma_e T$, where $i \sim V_b$ is electric flux (current), τ_e is relaxation time of currents, σ_e is electrical conductivity, or from results [5].

If there are other processes in the system that cause the corresponding changes in entropy, then $\Delta=\Delta_e+\Delta_{ext}$, where Δ_{ext} are the changes in entropy associated with other physical processes, for example, heat conduction.

If we write relation (9) using relations (6)-(8) for the nonequilibrium partition function (11) and expression (12), we obtain a transcendental equation for the parameter γ conjugate to $FPT T_\gamma$ in distribution (4). We want to express this parameter through the change in entropy $-\Delta=s_\gamma$, substitute it into expression (12) and obtain the connection between the average $FPT \bar{T}_\gamma$ and the change in entropy.

To write down an explicit solution to the transcendental equation, we expand the expressions included in it into a series to quadratic terms in γ . This expansion for expressions (11)-(12) has the form

$$\ln Z_\gamma \approx -\frac{N^*}{(\Gamma_+ - \Gamma_-)} [\gamma - \gamma^2 \frac{(\Gamma_+ + \Gamma_-)}{2(\Gamma_+ - \Gamma_-)^2}], \quad \gamma \bar{T}_\gamma \approx \frac{N^*}{(\Gamma_+ - \Gamma_-)} [\gamma - \gamma^2 \frac{(\Gamma_+ + \Gamma_-)}{2(\Gamma_+ - \Gamma_-)^2}], \quad \ln Z_\gamma + \gamma \bar{T}_\gamma \approx 0.$$

Equation (9) takes the form $-\Delta=s_\gamma=\beta u_\gamma$. What remains is the expression for βu_γ , the expansion for which has the form

$$\beta u_\gamma \approx \gamma^2 a + \gamma b, \quad (16)$$

$$a = -N^*(1.085 + \beta e V_b / 2 - \beta E_a) \frac{(\Gamma_+ + \Gamma_-)}{2(\Gamma_+ - \Gamma_-)^3} - \frac{N^*}{2(\Gamma_+ + \Gamma_-)^4} [(\Gamma_+ - \Gamma_-) \beta \frac{\partial(\Gamma_+ + \Gamma_-)}{\partial \beta} - 3(\Gamma_+ + \Gamma_-) \beta \frac{\partial(\Gamma_+ - \Gamma_-)}{\partial \beta}],$$

$$b = N^*(1.085 + \beta e V_b / 2 - \beta E_a) \frac{1}{(\Gamma_+ - \Gamma_-)} - N^* \frac{1}{(\Gamma_+ - \Gamma_-)^2} \beta \frac{\partial(\Gamma_+ - \Gamma_-)}{\partial \beta}.$$

In (16), the relation that follows from (14) is used: $\frac{\partial \Gamma_\pm}{\partial \beta} = \Gamma_\pm (-E_a \mp e V_b / 2)$, as well as the relation $\partial N^* / \partial \beta = N^* (-E_a + e V_b / 2 + 1.085 / \beta)$, where for the derivative with respect to β of the cumulant C_1 , proportional to the average current, the dependence of the electronic conductivity is taken in the form indicated in [30]. The expression for β uses the temperature T_{eff} from Table 1 in [5].

The solution to equation $-\Delta=s_\gamma=\beta u_\gamma$ with function (16) has the form

$$\gamma = (-b \pm \sqrt{b^2 - 4as_\gamma}) / 2a. \quad (17)$$

We select the “-” sign in (17), at which $\gamma|_{\Delta=0}=0$. When choosing the “+” sign, we obtain a stationary nonequilibrium state, which is realized at small negative values of γ .

Substituting this parameter γ (17) into an expression (12) makes it possible to find the value of the average FPT \bar{T}_γ at $s=\gamma$, obtained from distribution (4)-(6), depending on the change in entropy Δ_e in accordance with Eq. (9). Solution of equation (17) satisfy the condition $\gamma_{|\Delta=0} = 0$. We use the branch of solution (17) that corresponds to the positive values of the root expression in the denominator (12).

In relation (9) the value of $-\Delta$ is equal to the entropy changes within the system $\Delta S^{sys} = s_\gamma$. Let us determine this value using the relation

$$S_{tot} = \Delta S^{sys} + S^e, \quad (18)$$

where S_{tot} is the total change in entropy, S^e are the quantities responsible for the exchange of entropy with the environment. This value S^e was calculated using the expressions and data defined for the problem under consideration in [5]. In [5] is written “If the environment consists of several thermal reservoirs and local detailed balance holds, the mesoscopic entropy flow to these reservoirs $S^e(t) = -\sum_k Q_k(t)/T_k$, where $-Q_k(t)$ is the heat dissipated to a thermal reservoir at temperature T_k ”. In [5] expressions for $Q_k(t)$ are written for the situation under consideration, and also have used the definition of the entropy flow $S^e(t) = \log \Pi_{j=1}^{N(t)} \Gamma(n_{j-1} \rightarrow n_j) / \Gamma(n_j \rightarrow n_{j-1})$. Transition rates between different charge states of the double dot $\Gamma(n_{j-1} \rightarrow n_j)$ are given in [5]. The empirical transition rates are calculated using Eq. (D1) in [5], $\Gamma(n \rightarrow n') = N_{n \rightarrow n'} / P^{st}(n)\tau$, $N_{n \rightarrow n'}$ is the number of transitions from state n to state n' , $n \rightarrow n'$. All the data is obtained from counting statistics of experimental traces of durations of at least 1 hour. To obtain the stationary transition rates $\Gamma(n \rightarrow n')$ from the time trace $\{n_{tot}(t)\}$, in [5] (Supplement D) count the number of transitions $N_{n \rightarrow n'}$ that occur from state n to state n' for each bias voltage V_b value. In [5] calculate the transition rate between the states n and n' using [31] (D1) where τ is the time duration of the experiment and $P^{st}(n) = \tau_n / \tau$, (D2) [5] is the empirical steady-state occupation probability of the state n , calculated as the fraction of the total time when the double dot stays in state n . The traces of stochastic entropy production $s(t) = S_{tot}$ and of the entropy flow $S^e(t)$ are calculated using the empirical transitions rates (D1), occupation probabilities P^{st}_n (D2) from the time trace $\{n_{tot}(t)\}$. The expression (C10) $-\tilde{Q}_m^n / T_{el} = \ln \tilde{\Gamma}_m^n / \tilde{\Gamma}_n^m$ in [5], where the electronic temperature of the superconducting and normal-metal components $T_{el} \approx 170$ mK, as well as the values of T_{eff} from Table 1 in [5], are taken into account. The values S_{tot} are found from Table 2 in [5], they correspond to equation (1) in [5]. From (18) we find ΔS^{sys} (the last line in Table 1), we replace in expressions (16) - (17) $\Delta = S^{sys}$ with ΔS^{sys} and, using these data, we build Fig. 1-2.

The values of $\Delta_e = \Delta S^{sys} = s_\gamma$ change in entropy at different voltages are taken from Eq (18), Fig. 4, 12 and Table II [5]. Fig. 1 shows the dependences $T_0(N) = N/C_I$ (blue dashed line) and $\bar{T}_\gamma(\Delta_e) = \bar{T}_{\gamma(\Delta_e)}$ (red full line) for different values of N at bias voltage $V_b = 90 \mu V$. Let us consider external influences using the example of the applied bias voltage V_b . Fig. 2 shows the dependence of $\bar{T}_\gamma(\Delta_e)$ and T_0 on the applied voltage V_b at the level $N=10$.

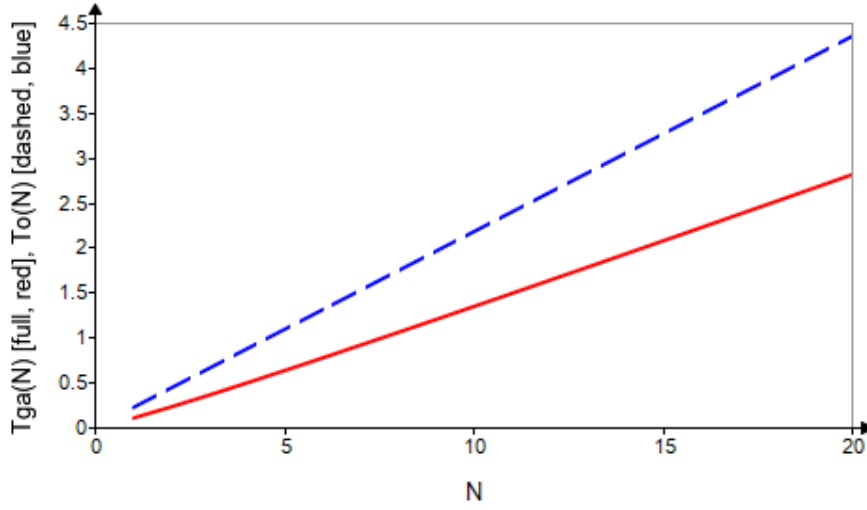


Fig. 1. Dependencies $T_0(N)=\bar{T}_{\gamma=0}=N/C_1$ (blue dashed line) and $Tga(N)=\bar{T}_{\gamma(\Delta_e)}=\bar{T}_{\gamma(\Delta)}$ (red full line approximating the calculated points) for the value N of the process $N(t)$ to take at a fixed time t . Regarding the random process of achieving a given value N , $N(t)$ is the net number of transmitted electrons [4, 5]. Bias voltage $V_b=90 \mu V$.

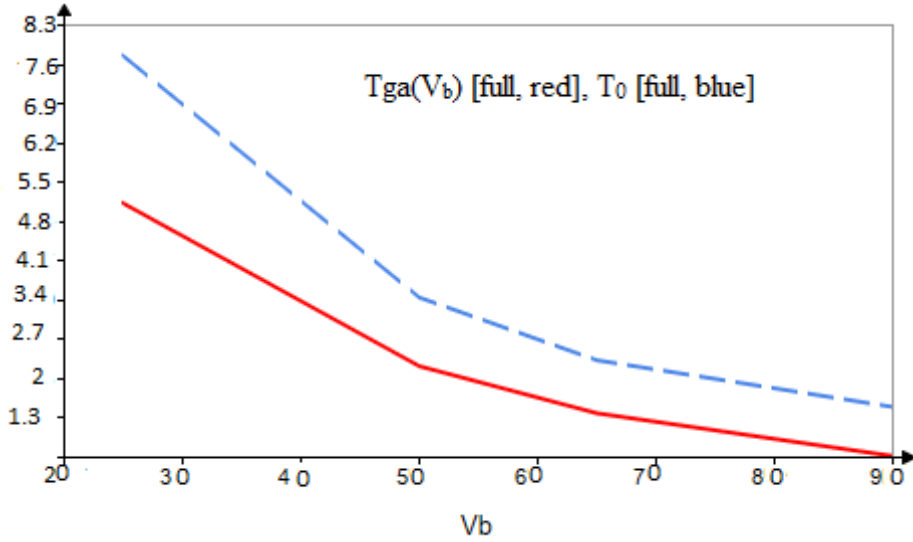


Fig.2. Calculated from relations (7)-(18) and Table 1 dependences of the average time $Tga(V=V_b)=\bar{T}_{\gamma(\Delta_e)}$ (red full line) and $T_0(V=V_b)=\bar{T}_{\gamma=0}=N/C_1$ (blue dashed line) to reach the level $N=10$ for different values of $V=V_b$ (25, 50, 65, 90 μV). The points in Fig. 2 calculated according to Table 1. $Tga(V_b)$ [full, red], T_0 [full, blue].

The figure is symmetrical about the y-axis for negative V_b values.

The data used in the calculations are summarized in Table 1.

Table 1.

$V_b \mu V$	90	65	50	25
$-\beta e V_b / 2$	0.522	0.32	0.23	0.093
$C_1 Hz$	4.6	3.25	2.48	1.23
$C_2 Hz$	9.27	8.725	8.48	8.23
$C_3=\alpha^2 C_1 Hz$	2.18	1.54	1.18	0.583
$\Gamma_+ Hz$	13.12	11.54	10.7	9.82
$\Gamma_- Hz$	6.439	6.846	7.1	7.55
$T_0 c$	2.17	3.077	4.037	8.13

$\bar{T}_{\gamma(\Delta_e)} c, N=10$	1.341	2.067	2.866	5.629
S_{tot}	1.83	0.95	0.6	0.31
ΔS^{sys}	1.79	0.8	0.41	0.16

Table 1. Used in the calculations of Fig. 2, the data obtained from relations (13) - (15) and expressions for the cumulant $Ci=1,2,3$ [4, 5].

5. Conclusion

The main purpose of this article: to show the need to take into account the change in entropy in *FPT*. The average *FPT* is associated with changes in entropy that occur during this process. The effect of such changes on the average *FPT* is shown using electrons transferred through a metallic double dot in the Coulomb-blockade as an example. The proposed approach makes it possible to take into account any other changes in entropy that correspond to other possible processes occurring in the system. The mean *FPT* values in accordance with expression (12) decrease when the system is influenced (for this process, $\gamma \geq 0$ and distribution (1)).

It is shown that the average *FPT* at zero value of the Laplace transform argument of the density distribution of the *FPT*, which is usually used to determine the average value of the *FPT*, does not reflect the influence of real processes on the average *FPT*. In Fig. 1 shows how taking into account the changes in entropy accompanying the process of the *FPT* affects the average value of *FPT*. In Fig. 2 shows how the applied voltage affects the system.

In this paper, the possibilities of taking into account the influence of entropy changes on the average *FPT* are shown. This is done on the basis of experimental results. It can be shown that this effect is different for different physical systems. For example, for neutrons in a nuclear reactor, the effect of changes in entropy on the reactor period during this period not so great for almost all values of the multiplication factor (with some exceptions) [32]. The influence of external influences is shown on the example of voltage affects. However, the effects can be very diverse (temperature effects, mechanical, etc.). The approach proposed in [3] opens up opportunities for the study of arbitrary influences by including them in changes in entropy. There are also opportunities to control the *FPT*, as noted in [3].

Data Availability Statement: The datasets generated during and/or analysed during the current study are available in the arxiv.org/abs/2201.06497 repository.

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